

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Kwang N. Kim, et al.

Application No.: TBD

Group Art Unit: TBD

Filed: TBD

Examiner: TBD

For: METHOD OF FORMING SILICON OXIDE  
LAYER AND METHOD OF  
MANUFACTURING THIN FILM  
TRANSISTOR THEREBY

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**FIRST PRELIMINARY AMENDMENT**

MS Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

**Amendments to the Specification** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 3 of this paper.